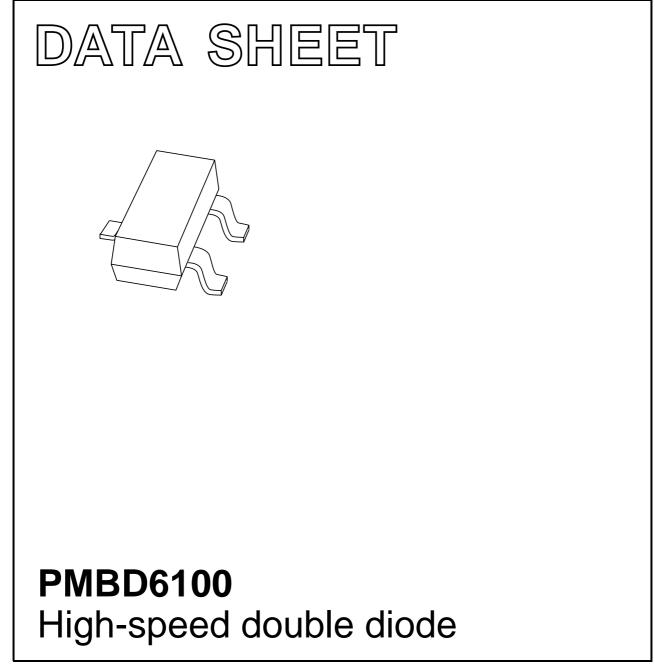
## DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 May 11 2003 Mar 25



### FEATURES

- Small plastic SMD package
- General applicationContinuous reverse voltage:

• High switching speed: max. 4 ns

- Continuous reverse voltage: max. 70 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 450 mA.

### **APPLICATIONS**

• High-speed switching in surface mounted circuits.

#### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>		
PMBD6100	*5B		

Note

1. \* = p : Made in Hong Kong.

\* = t : Made in Malaysia.

\* = W : Made in China.

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V <sub>RRM</sub>	repetitive peak reverse voltage		-	85	V
V <sub>R</sub>	continuous reverse voltage		-	70	V
l <sub>F</sub>	continuous forward current	single diode loaded; note 1; see Fig.2	-	215	mA
		double diode loaded; note 1; see Fig.2	-	125	mA

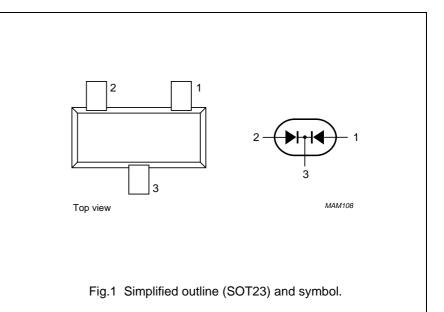
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### DESCRIPTION

The PMBD6100 consists of two high-speed switching diodes with common cathodes, fabricated in planar technology, and encapsulated in the small SOT23 plastic SMD package.

### PINNING

PIN	DESCRIPTION
1	anode (a1)
2	anode (a2)
3	common cathode



**PMBD6100** 

## PMBD6100

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>FRM</sub>	repetitive peak forward current		_	450	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; T <sub>j</sub> = 25 °C prior to surge; see Fig.4			
		t = 1 μs	-	4	А
		t = 1 ms	-	1	А
		t = 1 s	-	0.5	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	-	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

#### Note

1. Device mounted on an FR4 printed-circuit board.

### ELECTRICAL CHARACTERISTICS

 $T_j = 25 \ ^{\circ}C$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V <sub>F</sub>	forward voltage	see Fig.3			
		I <sub>F</sub> = 1 mA	550	700	mV
		I <sub>F</sub> = 10 mA	_	855	mV
		I <sub>F</sub> = 50 mA	_	1	V
		I <sub>F</sub> = 100 mA	0.85	1.1	V
I <sub>R</sub>	reverse current	see Fig.5			
		V <sub>R</sub> = 50 V	-	100	nA
		V <sub>R</sub> = 50 V; T <sub>j</sub> = 150 °C	-	50	μA
C <sub>d</sub>	diode capacitance	$f = 1 \text{ MHz}; V_R = 0; \text{ see Fig.6}$	_	1.5	pF
t <sub>rr</sub>	reverse recovery time	when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$ ; measured at $I_R = 1$ mA; see Fig.7	-	4	ns
V <sub>fr</sub>	forward recovery voltage	when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.8	-	1.75	V

### THERMAL CHARACTERISTICS

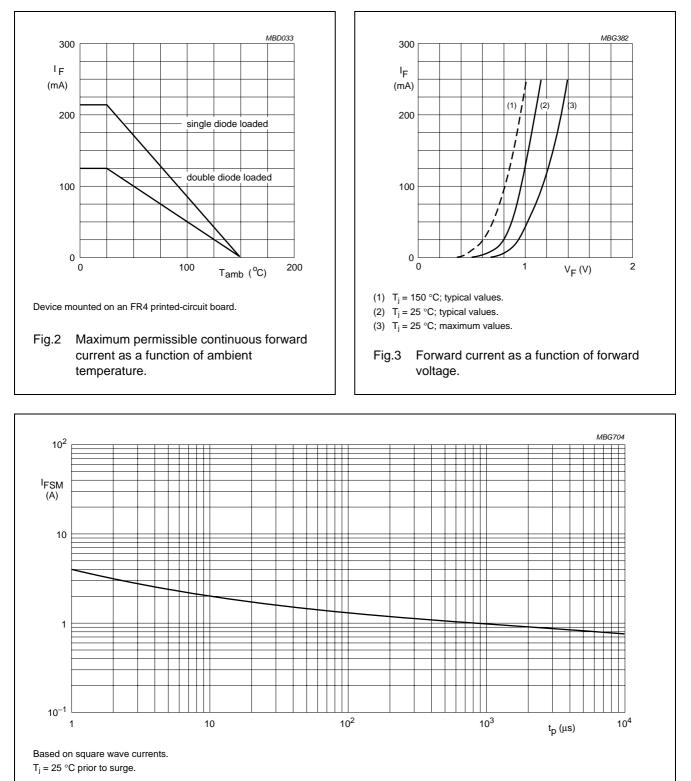
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point		360	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	500	K/W

### Note

1. Device mounted on an FR4 printed-circuit board.

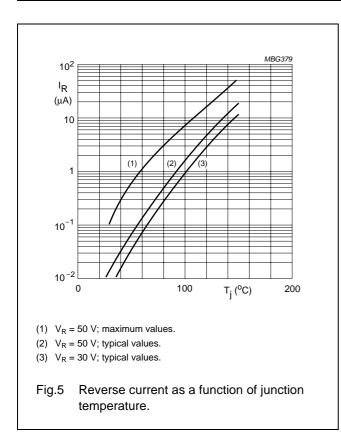
### PMBD6100

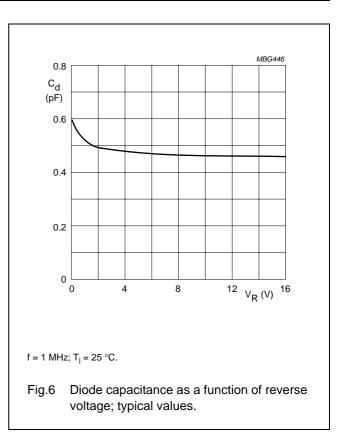
### **GRAPHICAL DATA**



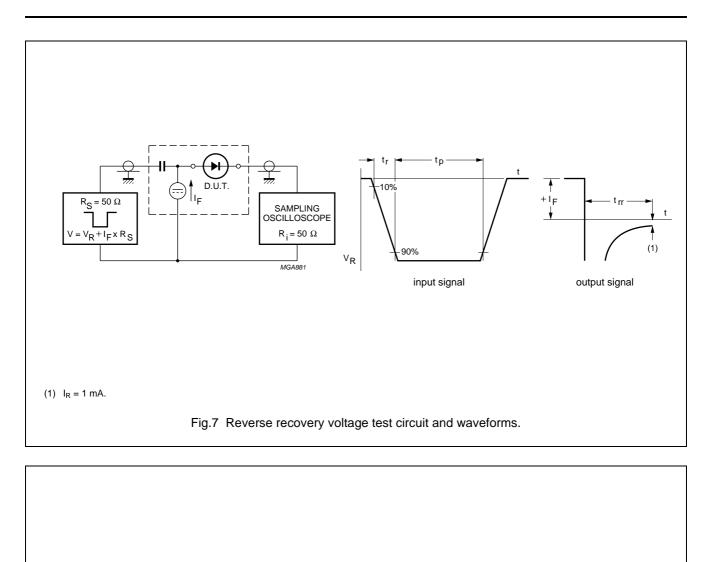


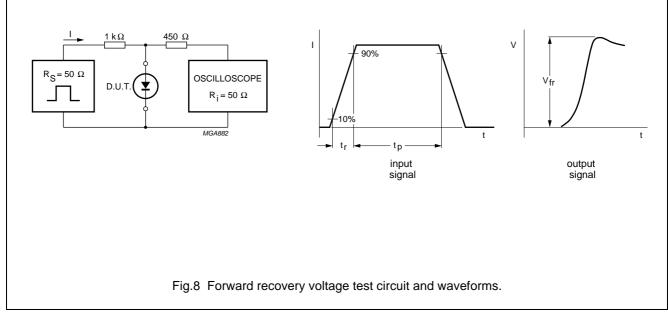
## PMBD6100





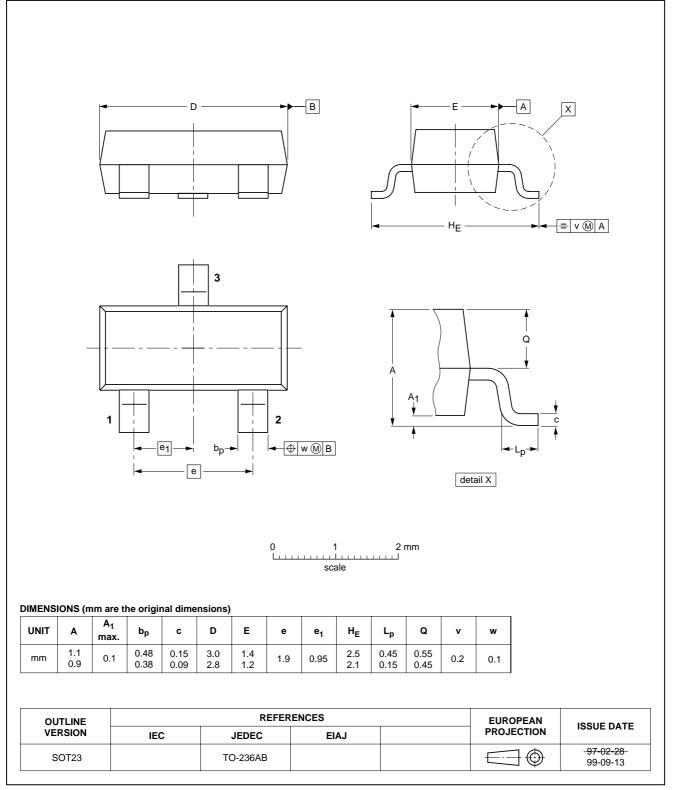
## PMBD6100





### PACKAGE OUTLINE





SOT23

PMBD6100

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### DATA SHEET STATUS

#### Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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## **NXP Semiconductors**

### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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